RF POWER FET TRANSISTOR

DESCRIPTION:

The ASI MRF182 is an RF power field effect transistor, N-Channel Enhancement-Mode lateral MOSFET.

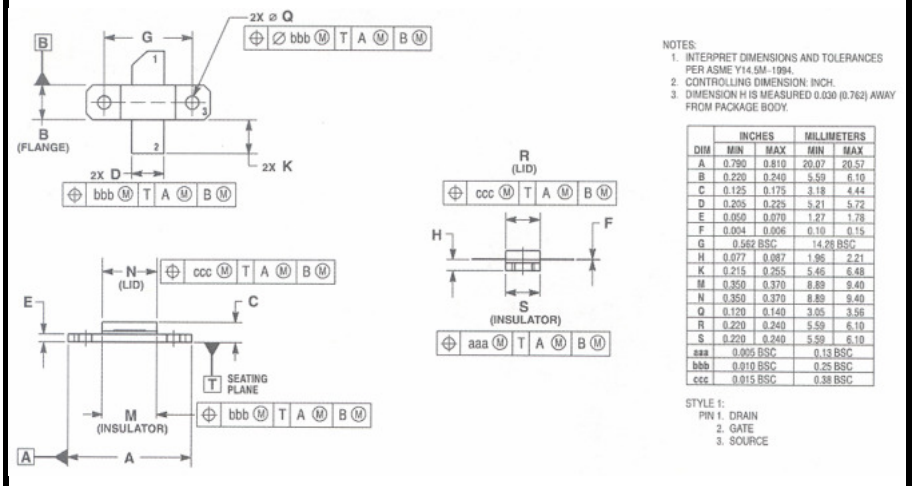
FEATURES INCLUDE:

- Bradband performance from HF to 1 GHz
- ***Omnigold***™ Metalization System
- High Gain, Rugged device.

MAXIMUM RATINGS

V_{DSS}	65 V
V_{GS}	±20 V
P_D	74 W @ T_C = 25 °C
T_J	-65 °C to +200 °C
T_{STG}	-65 °C to +150 °C
θ_{JC}	1.75 °C/W

PACKAGE STYLE .350 2L FLG



DIM	INCHES MIN	INCHES MAX	MILLIMETERS MIN	MILLIMETERS MAX
A	0.790	0.810	20.07	20.57
B	0.220	0.240	5.59	6.10
C	0.125	0.175	3.18	4.44
D	0.205	0.225	5.21	5.72
E	0.050	0.070	1.27	1.78
F	0.004	0.006	0.10	0.15
G	0.562 BSC		14.28 BSC	
H	0.077	0.087	1.96	2.21
K	0.215	0.255	5.46	6.48
M	0.350	0.370	8.89	9.40
N	0.350	0.370	8.89	9.40
Q	0.120	0.140	3.05	3.56
R	0.220	0.240	5.59	6.10
S	0.220	0.240	5.59	6.10
aaa	0.005 BSC		0.13 BSC	
bbb	0.010 BSC		0.25 BSC	
ccc	0.015 BSC		0.38 BSC	

CHARACTERISTICS T_C = 25 °C

SYMBOL	TEST CONDITIONS			MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{DSS}	I_D = 1.0 µA			65			V
I_{DSS}	V_{DS} = 28 V	V_{GS} = 0 V				1.0	µA
I_{GSS}	V_{DS} = 0 V	V_{GS} = 20 V				1.0	µA
$V_{GS(th)}$	V_{DS} = 10 V	I_D = 100 µA		2.0	3.0	4.0	V
$V_{GS(Q)}$	V_{DS} = 28 V	I_D = 50 mA		3.0	4.0	5.0	V
$V_{DS(on)}$	V_{GS} = 10 V	I_D = 3.0 A			0.9	1.2	V
g_{fs}	V_{DS} = 10 V	I_D = 3.0 A		1.6	1.8		S
C_{iss} C_{oss} C_{rss}	V_{DS} = 28 V	V_{GS} = 0 V	f = 1.0 MHz		56 28 2.5		pF
G_{PS}	V_{DD} = 28 V	P_{OUT} = 30 W	f = 945 MHz	11	14		dB
η	I_{DQ} = 50 mA			50	58		%